

• General Description

- AP4151 combines advanced MOSFET technology with a low resistance package to provide excellent $R_{\text{DS}(\text{ON})}$ and low gate charge.
- ESD Protected Gate

• Applications

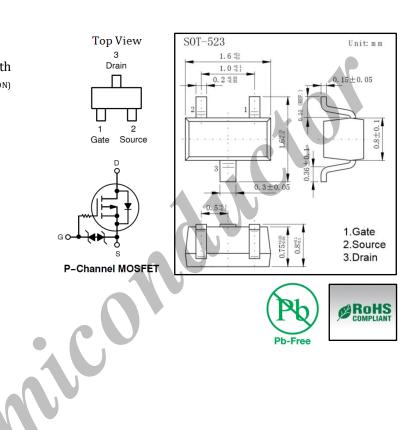
- Synchronous DC–DC conversion circuits
- High Side Load Switch
- Small Drive Circuit
- Battery Operated Systems such as Smart Phone

• Product Summary

V _{DS}	-20V
I_{D} (at $V_{GS} = -4.5V$)	-760mA
$R_{DS(ON)}$ (at $V_{GS} = -4.5V$)	< 260mΩ
$R_{DS(ON)}$ (at $V_{GS} = -2.5V$)	< 350mΩ
$R_{DS(ON)}$ (at $V_{GS} = -1.8V$)	<490mΩ

• Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit		
Drain-Source Voltage	V _{DS}	-20	V		
Gate-Source Voltage	V _{GS}	±6	V		
Continuous Drain Current	I _D	-760			
Pulsed Drain Current @ tp = 10μs	I _{DM}	-1000	mA		
Gate-to-Source RSD Rating (Human Body Model, Method 3015)	ESD	1800	V		
Power Dissipation (Steady State)	PD	301	mW		
Thermal Characteristics					
Thermal Resistance. Junction-to-Ambient (Steady State)	R _{0JA}	415	°C/W		
Lead Temperature for Soldering Purposes (1/8 in from case for 10s)	$T_{\rm L}$	260			
Operating Junction Temperature Range	TJ	-55 to 150	°C		
Storage Temperature Range	T _{STG}	-55 10 150			





• Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	V _{DSS}	I _D =-250μA, V _{GS} =0V	-20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-16V, V _{GS} =0V			-100	nA
Gate-Body Leakage Current	I _{GSS}	V_{DS} =0V, V_{GS} =±4.5V			±10	μA
Gate Threshold Voltage (Note 1)	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=-250\mu A$	-0.45		-1.2	V
		V _{GS} =-4.5V, I _D =-350mA		260	360	
Static Drain-Source On-Resistance (Note 1)	R _{DS(ON)}	V _{GS} =-2.5V, I _D =-300mA		350	450	mΩ
		V _{GS} =-1.8V, I _D =-150mA		490	1000	
Forward Transconductance (Note 1)	$\mathbf{g}_{ ext{FS}}$	V _{DS} =-10V, I _D =-250mA		0.4		S
Diode Forward Voltage	V _{SD}	I _S =-250mA, V _{GS} =0V			-1.1	V
Maximum Body-Diode Continuous Current	Is				-250	mA
Dynamic Parameters						
Input Capacitance	Ciss			156		
Output Capacitance	Coss	V_{GS} =0V, V_{DS} =-5V, f=1MHz		28		pF
Reverse Transfer Capacitance	C_{rss}			18		
Switching Parameters						
Total Gate Charge	Qg			2.1		
Threshold Gate Charge	Q _{gth}	V _{GS} =-4.5V, V _{DS} =-10V,		0.125		nC
Gate Source Charge	Qgs	I _D =-0.3A		0.325		IIC
Gate Drain Charge	\mathbf{Q}_{gd}			0.5		
Turn-On Delay Time	t _{D(on)}			8		
Turn-On Rise Time	tr	V _{GS} =-4.5V, V _{DS} =-10V,		8.2		na
Turn-Off Delay Time	t _{D(off)}	I _D =-200mA, R _G =10Ω		29		ns
Turn-Off Fall Time	t _f			20.4		

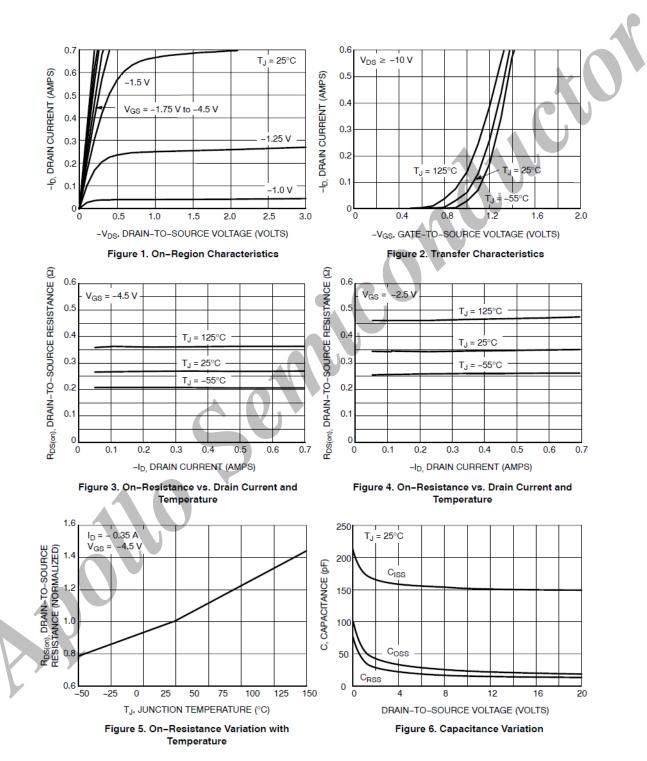
Note 1 - Pulse Test: pulse width \leq 300µs, duty cycle \leq 2%

• Ordering Information

Ordering Part Number	Package	MOQ
AP4151	SOT-523	3,000 pcs / reel

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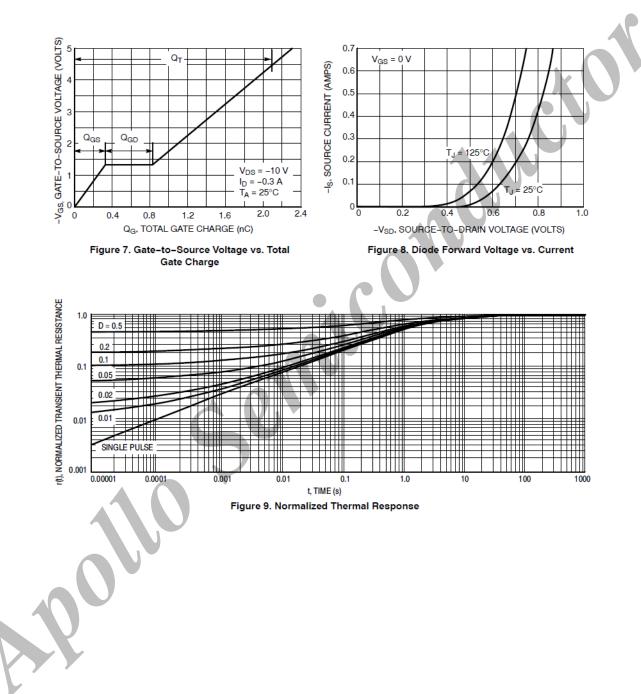




• Typical Electrical and Thermal Characteristics



AP4151 20V P-Channel Enhancement Mode MOSFET (ESD Protected Gate)



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AP4151 20V P-Channel Enhancement Mode MOSFET (ESD Protected Gate)

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